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(71) Applicant (for all designated States except US): KOREA  
RESEARCH INSTITUTE OF CHEMICAL TECH-  
NOLOGY [KR/KR]; #100, Jang-dong, Yuseong-gu,  
305-343 Daejeon (KR).

(72) Inventors; and

(75) Inventors/Applicants (for US only): KIM, Yunsoo  
[KR/KR]; #383-11, Doryong-dong, Yuseong-gu, 305-340  
Daejeon (KR). AN, Ki-Seok [KR/KR]; Hanmaeul Apt.  
101-1401, Songgang-dong, Yuseong-gu, 305-503 Dae-  
jeon (KR). LEE, Sun Sook [KR/KR]; Beodnae2danji  
Dongyang Apt. 206-2002, Taepyung-2-dong, Jung-gu,

301-152 Daejeon (KR). CHUNG, Taek-Mo [KR/KR];  
Gongdonggwalli Apt. 6-203, #431, Doryong-dong,  
Yuseong-gu, 305-340 Daejeon (KR). CHO, Wontae  
[KR/KR]; Sanga Apt. 105-1304, Kwangan-1-dong,  
Suyoung-gu, 613-101 Busan (KR). SUNG, Kiwhan  
[KR/KR]; Daedong Apt. 201-1310, Seonhak-dong,  
Yeonsu-gu, 406-090 Incheon (KR).

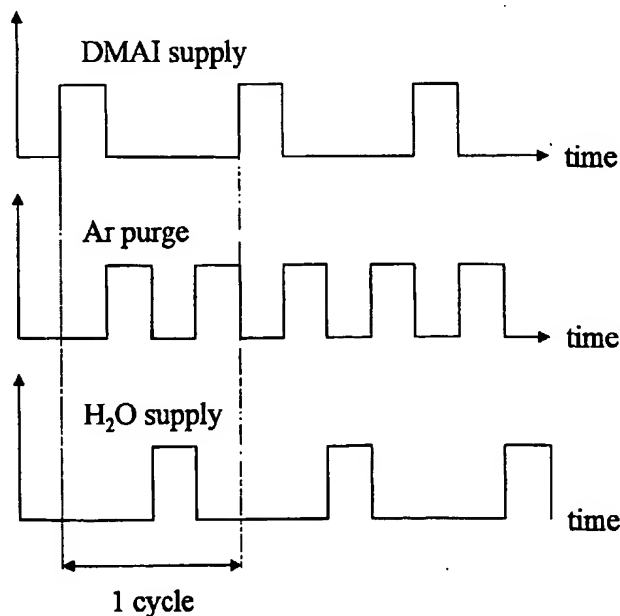
(74) Agents: JANG, Seongku et al.; 19th Fl., KEC Building,  
275-7, Yangjae-dong, Seocho-ku, Seoul 137-130 (KR).

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(54) Title: METHOD FOR PREPARATION OF ALUMINUM OXIDE THIN FILM



(57) Abstract: An aluminum oxide film is formed on a substrate by a process comprising A) bringing the vapor of a dialkylaluminum alkoxide into contact with the substrate mounted in a deposition reactor so that an aluminum-containing adsorption layer is formed on the substrate; B) removing the unreacted aluminum compound and by-products from the reactor; C) introducing an oxygen source into the reactor so that the oxygen source reacts with the aluminum-containing adsorption layer to form an aluminum oxide layer; and D) removing the unreacted oxygen source and by-products from the reactor.

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